

PTO/SB/08A (10/01) (Substitute for form 1449A/PTO)		ATTY. DOCKET NO. COVA0003 DIV Client/Matter No. 90337.0006.001		APPLICATION NO. _____	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) Sheet <u>1</u> of <u>5</u>		FIRST NAMED INVENTOR Klaus Dimmler, Alfred P. Gnadinger			
		FILING DATE Herewith		ART UNIT	

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document No. No. - Kind Code	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Doc	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
<div style="font-size: 2em; font-weight: bold; margin-bottom: 10px;">LP</div> <div style="border-left: 2px solid black; height: 100%; position: relative;"> <div style="position: absolute; bottom: 0; left: -10px; font-size: 2em;">✓</div> </div>		US-3,832,700	08/27/1974	Wu et al.	
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<div style="font-size: 2em; font-weight: bold; margin-top: 10px;">LP</div> <div style="border-left: 1px solid black; height: 100%; position: relative; margin-top: 10px;"> <div style="position: absolute; bottom: 0; left: -10px;">↓</div> </div>		US-6,151,241	11/21/2000	Hayashi et al.	
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		US-5,780,886	07/14/1998	Yamanobe et al.	Figures 1(A)-4(C)
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LP		JP 408055919 A	02/27/1996	Ogimoto et al.		YES	NO
LP		WO98/98/13300	02/04/1998	Kawamura			

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s) publisher, city and/or country where published
LP		TOKUMITSU, EISUKE et al, "Characterization of MF(M)IS structures using P(L)ZT and Y ₂ O ₃ films", Jpn. J. of Appl.Phys., Vol 39, September 2000, pp. 5456-5459.
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EXAMINER SIGNATURE		<u>Long Pham</u>	DATE CONSIDERED <u>3/6/04</u>
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			